L Number	Hits	Search Text	DB	Time stamp
5	1946	(laminar with (flow or flowing)) and semiconductor	USPAT	2004/03/03 13:04
6	2979	(laminar with (flow or flowing)) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/03 13:08
7	2139	((laminar with (flow or flowing)) and semiconductor) and @ay<=2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/03 13:05
8	180	(((laminar with (flow or flowing)) and semiconductor) and @ay<=2000) and (polish or polishing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/03 13:06
9	8	schwab-Gunter.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/03 13:06
10	15	Franke-Helmut.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/03 13:06
11	1	Schofberger-Manfred.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/03 13:07
12	0	6596599.pn. and (shield same edge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/03 13:07
13	0	6596599.pn. and shield	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/03 13:07
14	2153	((laminar with (flow or flowing)) and semiconductor) not plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/03 13:08
15	913	(((laminar with (flow or flowing)) and semiconductor) not plasma) and edge	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/03 13:08
16	42	((((laminar with (flow or flowing)) and semiconductor) not plasma) and edge) and ((etch or etching) same laminar)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/03 13:09

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